DATA SHEET

For a complete data sheet, please also download:

- The IC06 74HC/HCT/HCU/HCMOS Logic Family Specifications
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Information
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Outlines

74HC/HCT10

Triple 3-input NAND gate

Product specification

File under Integrated Circuits, IC06

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Philips Semiconductors

PHILIPS

Triple 3-input NAND gate

74HC/HCT10

FEATURES

- Output capability: standard
- I_{CC} category: SSI

GENERAL DESCRIPTION

The 74HC/HCT10 are high-speed Si-gate CMOS devices and are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT10 provide the 3-input NAND function.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; t_r = t_f = 6 ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC	HCT	
t_{PHL}/ t_{PLH}	propagation delay nA, nB, nC to nY	C_L = 15 pF; V_{CC} = 5 V	9	11	ns
C_I	input capacitance		3.5	3.5	pF
C_{PD}	power dissipation capacitance per gate	notes 1 and 2	12	14	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

   $$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_O) \text{ where:}$$

   f_i = input frequency in MHz

   f_o = output frequency in MHz

   C_L = output load capacitance in pF

   V_{CC} = supply voltage in V

   $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

2. For HC the condition is V_I = GND to V_{CC}

   For HCT the condition is V_I = GND to V_{CC} − 1.5 V.

ORDERING INFORMATION

See *"74HC/HCT/HCU/HCMOS Logic Package Information"*.

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PIN DESCRIPTION

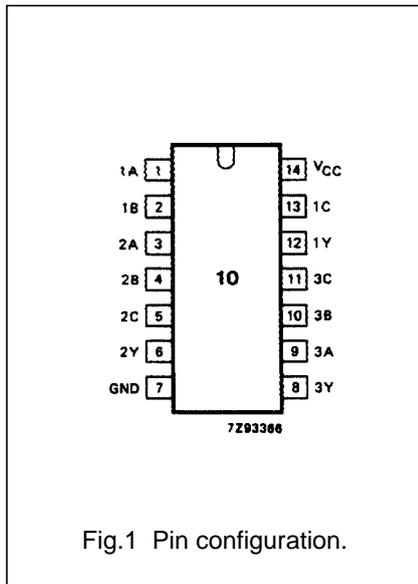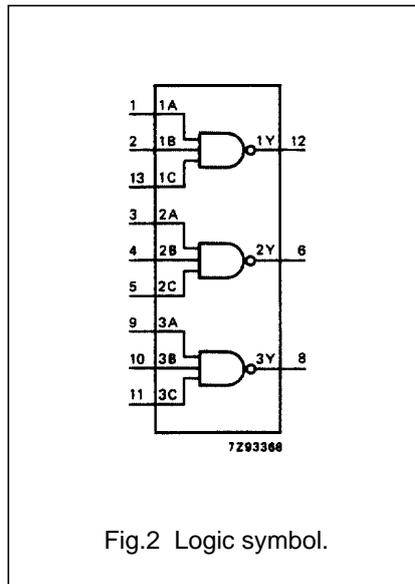| PIN NO.	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A to 3A	data inputs
2, 4, 10	1B to 3B	data inputs
13, 5, 11	1C to 3C	data inputs
12, 6, 8	1Y to 3Y	data outputs
7	GND	ground (0 V)
14	V_{CC}	positive supply voltage

Fig.1 Pin configuration.

Fig.2 Logic symbol.
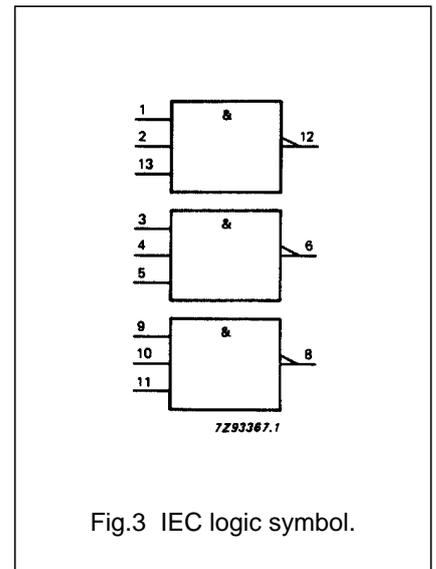
Fig.3 IEC logic symbol.
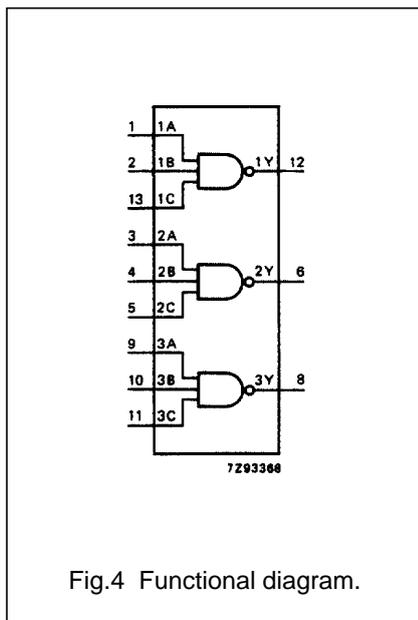
Fig.4 Functional diagram.
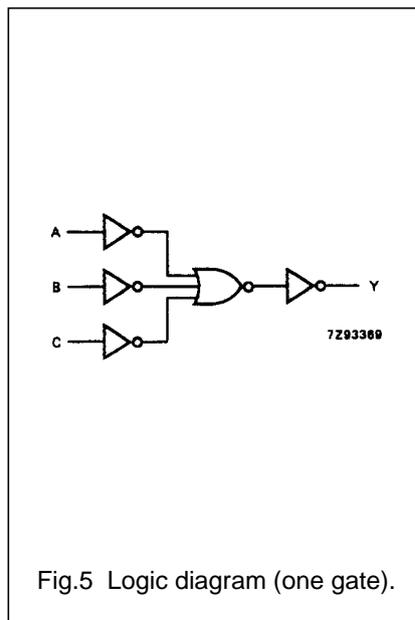
Fig.5 Logic diagram (one gate).

FUNCTION TABLE

INPUTS			OUTPUT
nA	nB	nC	nY
L	L	L	H
L	L	H	H
L	H	L	H
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	L

Notes

1. H = HIGH voltage level
    L = LOW voltage level

Triple 3-input NAND gate   74HC/HCT10

DC CHARACTERISTICS FOR 74HC

For the DC characteristics see *"74HC/HCT/HCU/HCMOS Logic Family Specifications"*.

Output capability: standard
I_{CC} category: SSI

AC CHARACTERISTICS FOR 74HC

GND = 0 V; t_r = t_f = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C) 74HC						UNIT	TEST CONDITIONS	
		+25			−40 to + 85		−40 to + 125		V_{CC} (V)	WAVEFORMS
		min.	typ.	max.	min.	max.	min.	max.		
t_{PHL}/ t_{PLH}	propagation delay nA, nB, nC to nY		30	95		120		145	ns	2.0	Fig.6
			11	19		24		29		4.5	
			9	16		20		25		6.0	
t_{THL}/ t_{TLH}	output transition time		19	75		95		110	ns	2.0	Fig.6
			7	15		19		22		4.5	
			6	13		16		19		6.0	

Triple 3-input NAND gate

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DC CHARACTERISTICS FOR 74HCT

For the DC characteristics see *"74HC/HCT/HCU/HCMOS Logic Family Specifications"*.

Output capability: standard
I_{CC} category: SSI

Note to HCT types

The value of additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given in the family specifications.
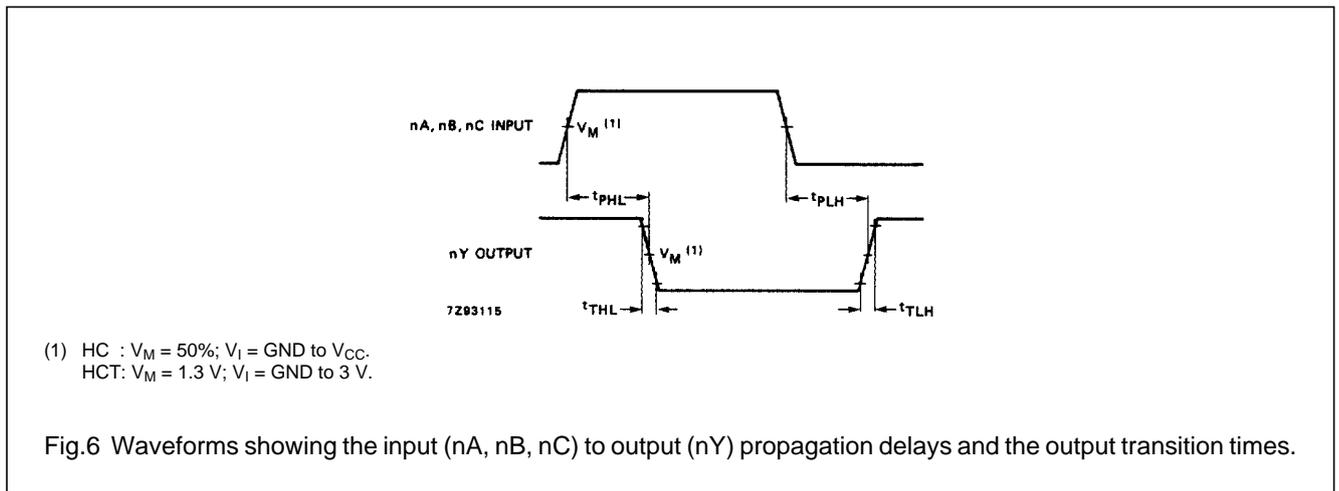To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in the table below.

INPUT	UNIT LOAD COEFFICIENT
nA, nB, nC	1.5

AC CHARACTERISTICS FOR 74HCT

GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS	
		74HCT								V_{CC} (V)	WAVEFORMS
		+ 25			−40 to + 85		−40 to +125				
		min.	typ.	max.	min.	max.	min.	max.			
t_{PHL}/ t_{PLH}	propagation delay nA, nB, nC to nY		14	24		30		36	ns	4.5	Fig.6
t_{THL}/ t_{TLH}	output transition time		7	15		19		22	ns	4.5	Fig.6

AC WAVEFORMS

(1) HC : V_M = 50%; V_I = GND to V_{CC}.
    HCT: V_M = 1.3 V; V_I = GND to 3 V.

Fig.6 Waveforms showing the input (nA, nB, nC) to output (nY) propagation delays and the output transition times.

PACKAGE OUTLINES

See *"74HC/HCT/HCU/HCMOS Logic Package Outlines"*.